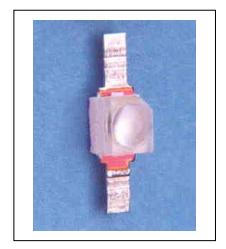
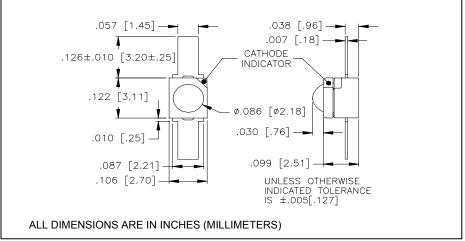
CLE110F

Gallium Arsenide IRED Flat Lead PLCC Package



April, 2003





features

- Flat lead PLCC package
- ± 5° emission angle
- 940 nm peak wavelength
- · Collimating plastic lens
- · Available with flat window

description

The CLE110F infrared emitting diode features current GaAs/AlGaAs technology for increased quantum efficiency. The chip is mounted in a compact, embedded leadframe package with flying lead configuration. The plastic lens provides a narrow emission pattern. Contact Clairex for alternative wavelength emitter chips, different lens and lead configurations.

absolute maximum ratings (T_A = 25°C unless otherwise stated)

storage temperature	40°C to +125°C
operating temperature	40°C to +100°C
operating temperaturelead soldering temperature ⁽¹⁾	260°C
continuous forward current ⁽²⁾	30mA
peak forward current (1.0ms pulse width, 10% duty cycle)	1A
reverse voltage	5V
reverse voltage	75mW

notes:

- 1. 0.06" (1.5mm) from case for 5 seconds maximum.
- 2. Derate linearly $0.32\text{mA/}^{\circ}\text{C}$ from 25°C free air temperature to $T_A = +100^{\circ}\text{C}$.
- 3. Derate linearly 0.80mW/°C from 25°C free air temperature to $T_A = +100$ °C.

lectrical characteristics (T _A = 25°C unless otherwise noted)							
symbol	parameter	min	typ	max	units	test conditions	
Po	Total power output	2.0	2.5	-	mW	I _F = 20mA	
V _F	Forward voltage	-	-	1.5	V	I _F = 20mA	
I _R	Reverse current	-	-	10	μΑ	V _R = 5.0V	
λρ	Peak emission wavelength	-	940	-	nm	I _F = 20mA	
BW	Spectral bandwidth at half power points	-	50	-	nm	I _F = 20mA	
θнР	Emission angle at half power points	-	10	-	deg.	I _F = 20mA	
t _r , t _f	Radiation rise and fall time	-	700	-	ns	I _{F(PK)} = 20mA	

Clairex reserves the right to make changes at any time to improve design and to provide the best possible product.

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